

CBCS Scheme

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17ELN15

First Semester B.E. Degree Examination, Dec.2017/Jan.2018 Basic Electronics

Time: 3 hrs.

Max. Marks: 100

Note: Answer any FIVE full questions, choosing one full question from each module.

Module-1

- 1 a. Explain the operation of PN junction diode under forward and reverse biased conditions, with the help of VI characteristics curve. (06 Marks)
- b. Derive the relation between α and β . Calculate I_C and I_E for transistor that has $\alpha_{dc} = 0.98$ and $I_B = 100 \mu A$. (06 Marks)
- c. With a neat circuit diagram and waveforms, explain the working of centre-tap full wave rectifier and derive the efficiency for the same. (08 Marks)

OR

- 2 a. With a neat diagram, explain the operation of PNP and NPN transistor. (08 Marks)
- b. A half wave rectifier from a supply 230 V 50 Hz with step down transformer ratio 3:1 to a resistive load of 10 K Ω . The diode forward resistance is 75 Ω and transformer secondary is 10 Ω . Calculate the DC current, DC voltage, efficiency and ripple factor. (06 Marks)
- c. With neat circuit diagram, explain the common emitter circuit and sketch the input and output characteristics. (06 Marks)

Module-2

- 3 a. With a necessary equation and circuit, explain the base-bias transistor circuits. (06 Marks)
- b. Design an Adder using op-amp to give the output voltage,
 $V_o = -[2V_1 + 3V_2 + 5V_3]$ (06 Marks)
- c. Derive the equations for output voltage for an inverting amplifier and an integrator. (08 Marks)

OR

- 4 a. Explain the characteristics of an ideal op-amp. Mention the applications. (06 Marks)
- b. Accurately analyze the voltage divider bias which has $V_{CC} = 18 V$, $R_1 = 33 K\Omega$, $R_2 = 12 K\Omega$ and $R_E = 1 K\Omega$. Determine V_E , V_C , V_{CE} , I_C and Q point, when transistor $h_{fe} = 200$. (08 Marks)
- c. Write short notes on op-amp virtual ground concept. (06 Marks)

Module-3

- 5 a. Perform the following:
 - i) Convert $(57345)_{10} = (\quad)_{16}$
 - ii) Subtract $(28)_{10} - (19)_{10}$ using 2's complement method. (06 Marks)
- b. Realize $Y = AB + CD + E$ using NAND gate. (06 Marks)
- c. Explain the full adder circuit with truth table. Realize the circuit for sum and carry using logic gates. (08 Marks)

OR

- 6 a. Perform the following:
- Convert $(FA27D)_{16} = ()_2 \rightarrow = ()_8 = ()_{10}$
 - Subtract $10.0101 - 101.1110$ using 1's complement method. (06 Marks)
- b. $Y = A + AB + ABC$ simplify and implement using logic gates and NOR gates. (06 Marks)
- c. State and prove De Morgan's theorem using two variable. (08 Marks)

Module-4

- 7 a. Bring out differences between flip flops and latches. (04 Marks)
- b. Explain SR flipflop with circuit diagram and truth table. (06 Marks)
- c. With a neat block diagram explain the architecture of 8051 microcontroller. (10 Marks)

OR

- 8 a. Explain the operation of NAND gate latch with circuit and truth table. (10 Marks)
- b. What is stepper motor? With a neat block diagram, explain the working principle of microcontroller based stepper motor control system. (10 Marks)

Module-5

- 9 a. Define communication. With neat block diagram, explain the elements of communication system. (06 Marks)
- b. Derive an expression for amplitude modulation and draw the necessary waveforms. (08 Marks)
- c. What is transducer? Compare the active and passive transducers. (06 Marks)

OR

- 10 a. Bring out the difference between amplitude modulation and frequency modulation. (06 Marks)
- b. If a FM wave represented by the equation $V = 10\sin(8 \times 10^8 + 4\sin 1000t)$, calculate:
- Carrier frequency
 - Modulating frequency
 - Modulation index
 - Band width
- (06 Marks)
- c. With necessary diagram and equations, explain the following:
- Piezo-electric transducer
 - LVDT.
- (08 Marks)

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